

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
Q1	30V	27m Ω @ $V_{GS} = 10\text{V}$	7.2A
		35m Ω @ $V_{GS} = 4.5\text{V}$	6.0A
Q2	-30V	25m Ω @ $V_{GS} = -10\text{V}$	-7.6A
		41m Ω @ $V_{GS} = -4.5\text{V}$	-6.2A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

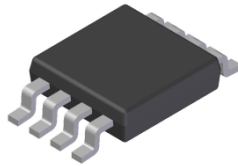
- DC-DC Converters
- Power Management Functions
- Backlighting

Features and Benefits

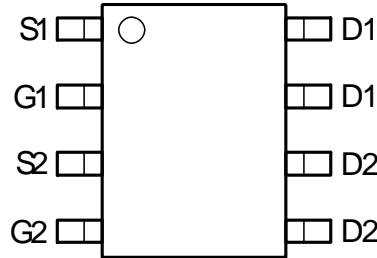
- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMC3028LSDXQ](#))**

Mechanical Data

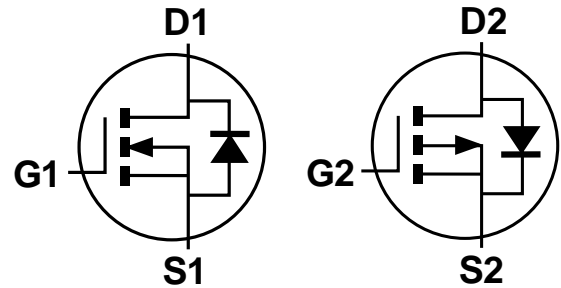
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (Approximate)



Top View



Top View
Pin Configuration



Equivalent Circuit

Q N-Channel MOSFET

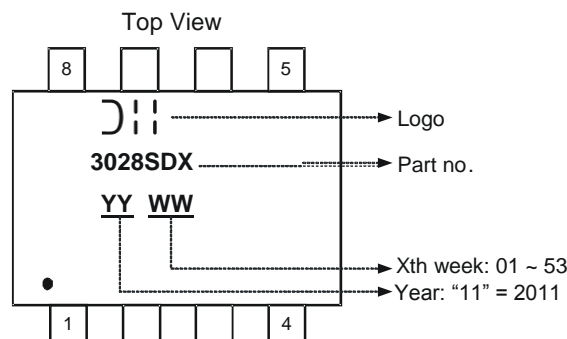
Q2 P-Channel MOSFET

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC3028LSDX-13	SO-8	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Maximum Ratings – Q1 and Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1	Q2	Units
Drain-Source Voltage			V _{DSS}	30	-30	V
Gate-Source Voltage			V _{GSS}	±20	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	5.5 4.1	-5.8 -4.3	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	7.2 5.7	-7.6 -6.1	A
Maximum Body Diode Forward Current (Note 5)			I _S	2.2	-2.2	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	40	-30	A
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	14.5	-22	A
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	10.5	25	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1.2	W
	T _A = +70°C		0.75	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	108	°C/W
	t < 10s		65	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.5	W
	T _A = +70°C		0.95	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	85	°C/W
	t < 10s		50	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	14.5	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics – Q1 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	1	—	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	19	27	mΩ	V _{GS} = 10V, I _D = 6A
		—	22	35		V _{GS} = 4.5V, I _D = 5A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1.3A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	641	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	66	—		
Reverse Transfer Capacitance	C _{rss}	—	51	—		
Gate Resistance	R _G	—	2.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	6	—	nC	V _{DS} = 15V, I _D = 10A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	13.2	—		
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	2.2	—		
Turn-On Delay Time	t _{D(on)}	—	3.3	—	nS	V _{GS} = 10V, V _{DD} = 15V, R _G = 6Ω, I _D = 1A
Turn-On Rise Time	t _r	—	4.4	—		
Turn-Off Delay Time	t _{D(off)}	—	22.3	—		
Turn-Off Fall Time	t _f	—	5.3	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

Electrical Characteristics – Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(th)}	-1	—	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	21	25	mΩ	V _{GS} = -10V, I _D = -6A
		—	29	41		V _{GS} = -4.5V, I _D = -5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1.3A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{ISS}	—	1,241	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{OSS}	—	146	—		
Reverse Transfer Capacitance	C _{RSS}	—	110	—		
Gate Resistance	R _G	—	14.8	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	10.9	—	nC	V _{DS} = -15V, I _D = -7A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	22	—		
Gate-Source Charge	Q _{gs}	—	3.5	—		
Gate-Drain Charge	Q _{gd}	—	4.7	—		
Turn-On Delay Time	t _{D(on)}	—	9.7	—	nS	V _{GS} = -10V, V _{DD} = -15V, R _{GEN} = 6Ω, I _D = -7A
Turn-On Rise Time	t _r	—	17.1	—		
Turn-Off Delay Time	t _{D(off)}	—	60.5	—		
Turn-Off Fall Time	t _f	—	40.4	—		

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

N-Channel – Q1

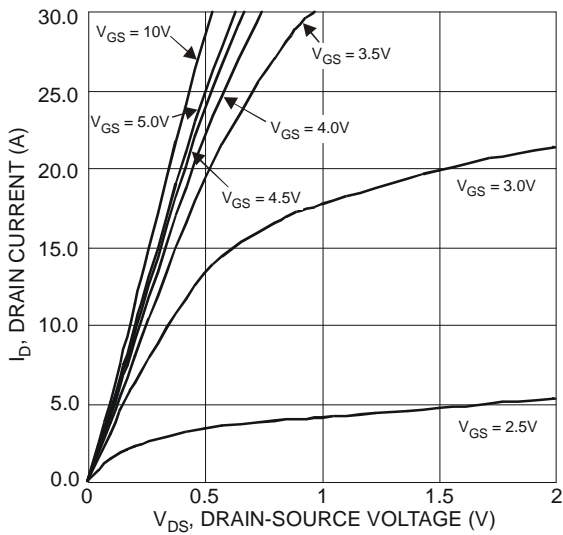


Figure 1 Typical Output Characteristic

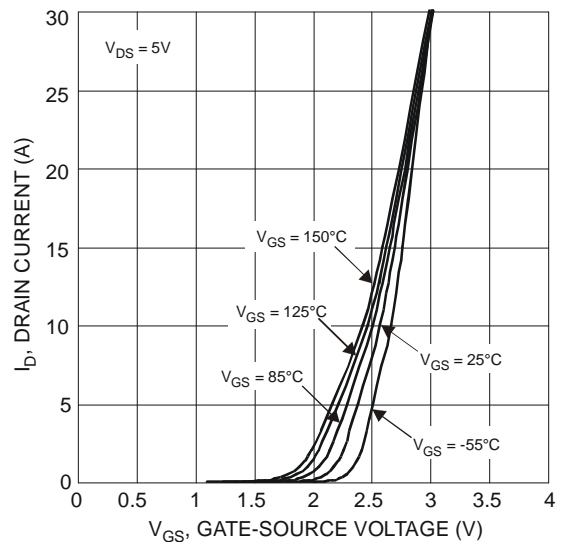


Figure 2 Typical Transfer Characteristic

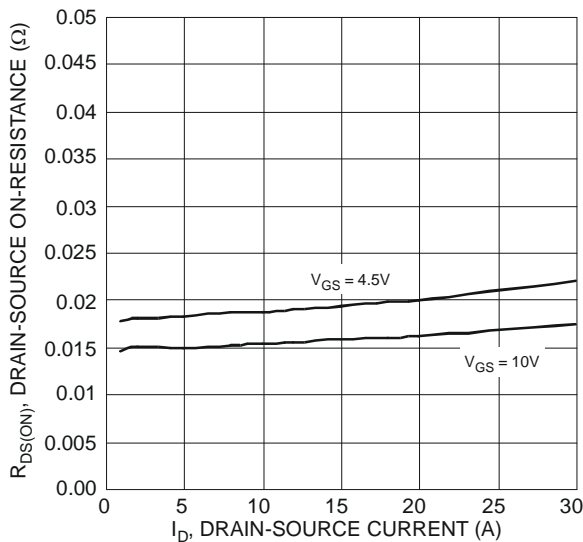


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

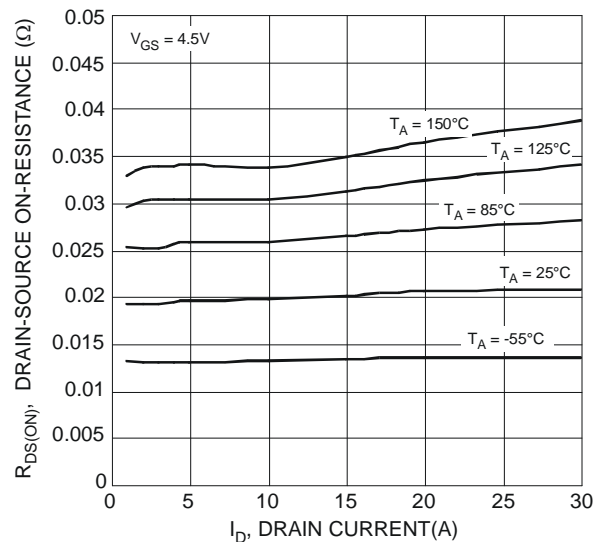


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

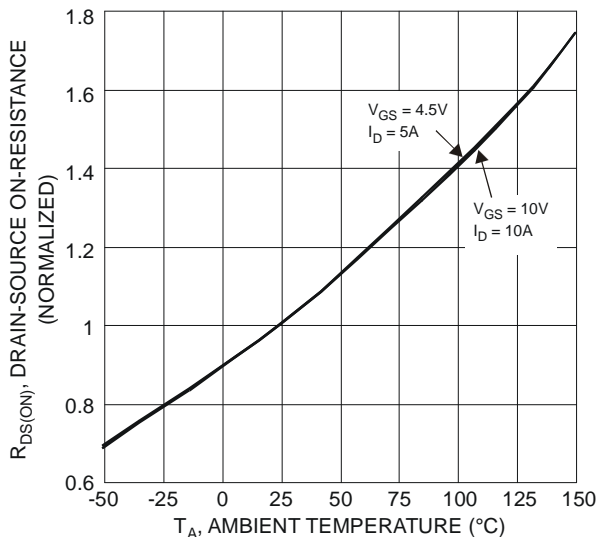


Figure 5 On-Resistance Variation with Temperature

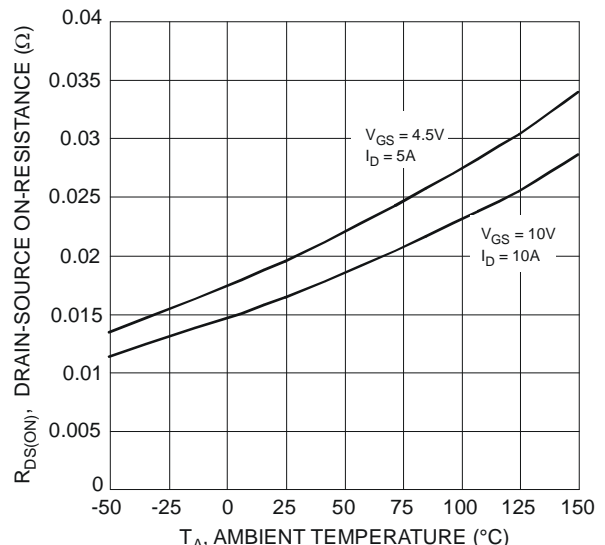


Figure 6 On-Resistance Variation with Temperature

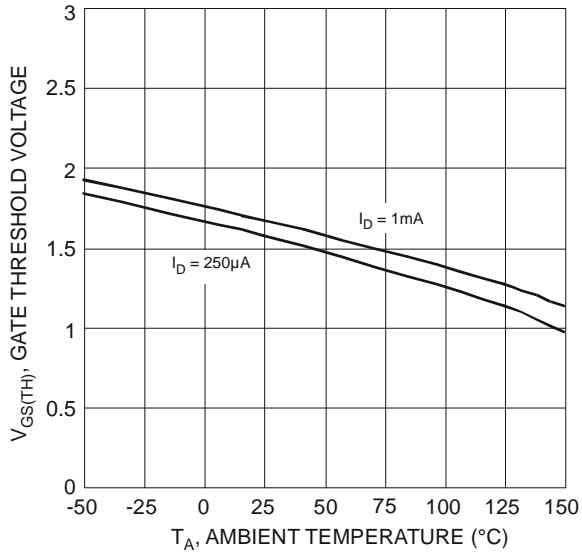


Figure 7 Gate Threshold Variation vs. Ambient Temperature

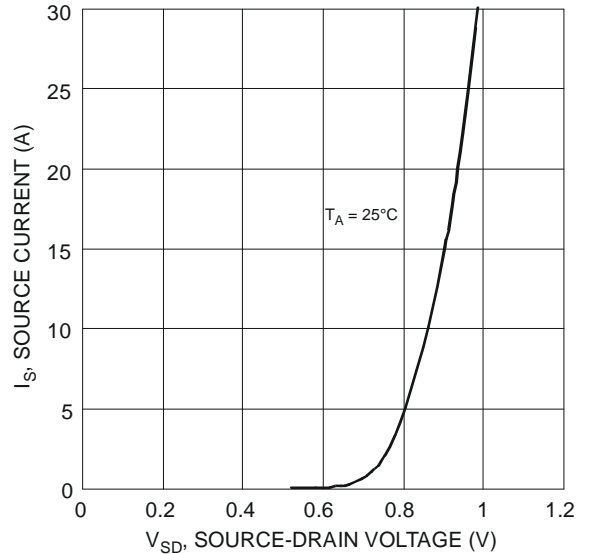


Figure 8 Diode Forward Voltage vs. Current

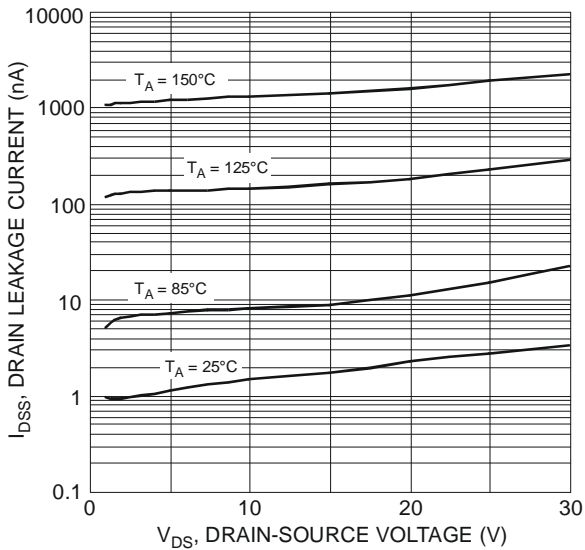


Figure 9 Typical Drain-Source Leakage Current vs. Voltage

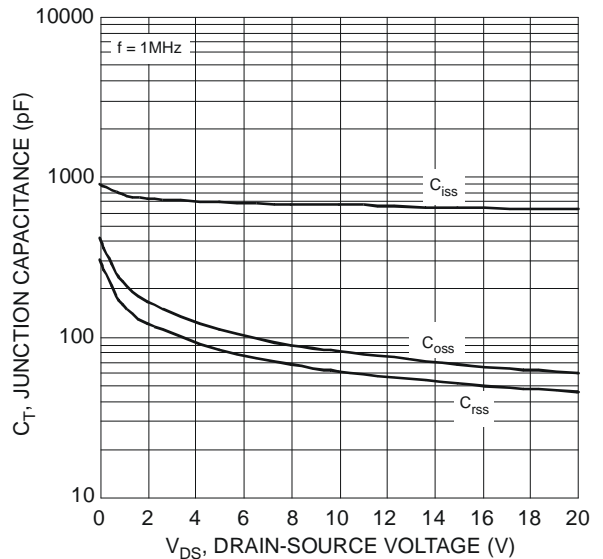


Figure 10 Typical Junction Capacitance

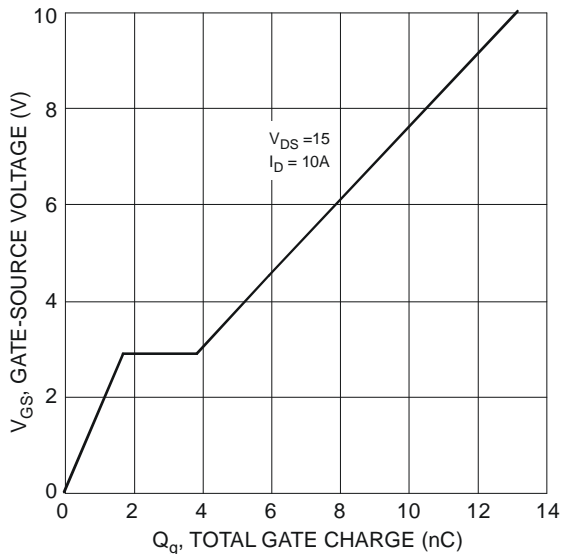


Figure 11 Gate-Source Voltage vs. Total Gate Charge

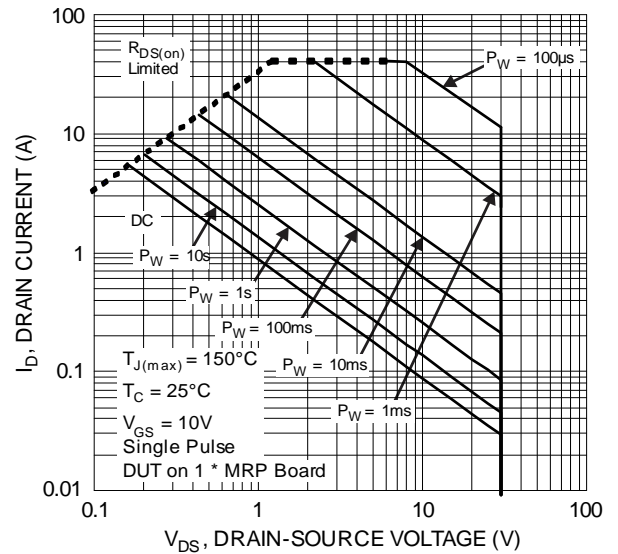


Figure 12 SOA, Safe Operation Area

P-Channel – Q2

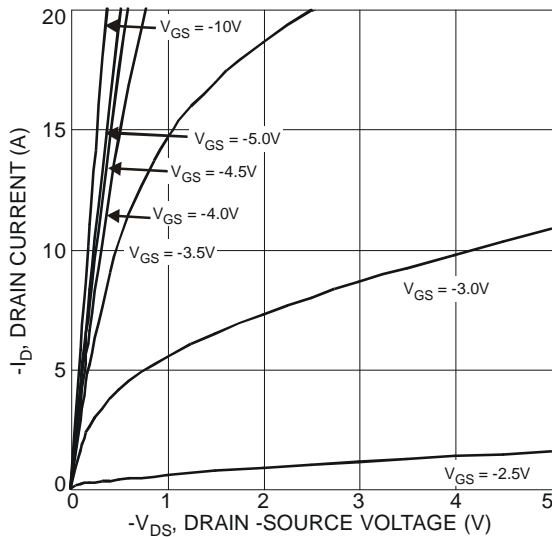


Figure 1 Typical Output Characteristics

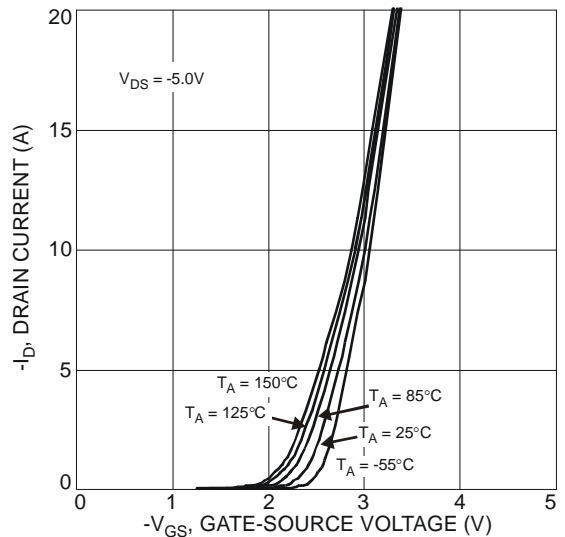


Figure 2 Typical Transfer Characteristics

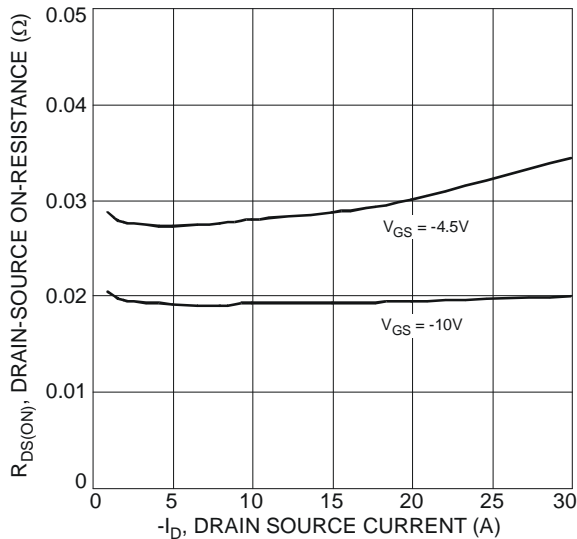


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

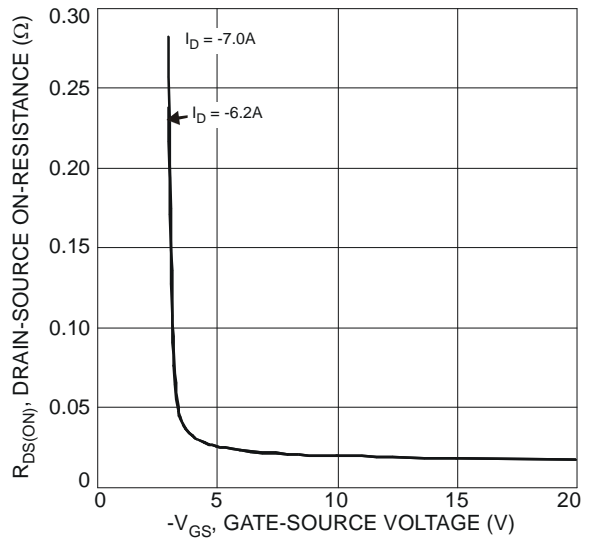


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

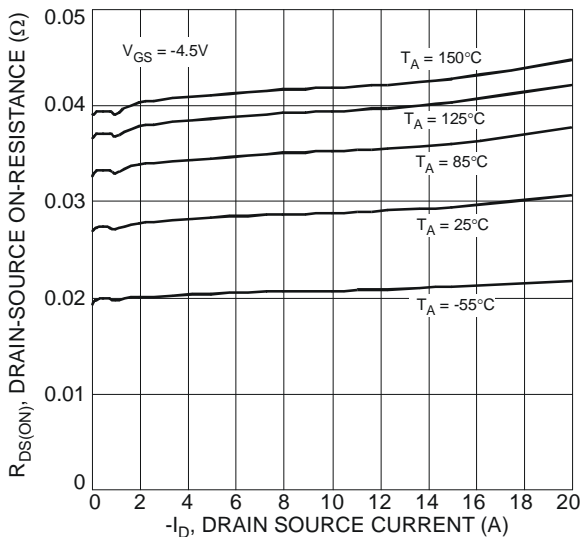


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

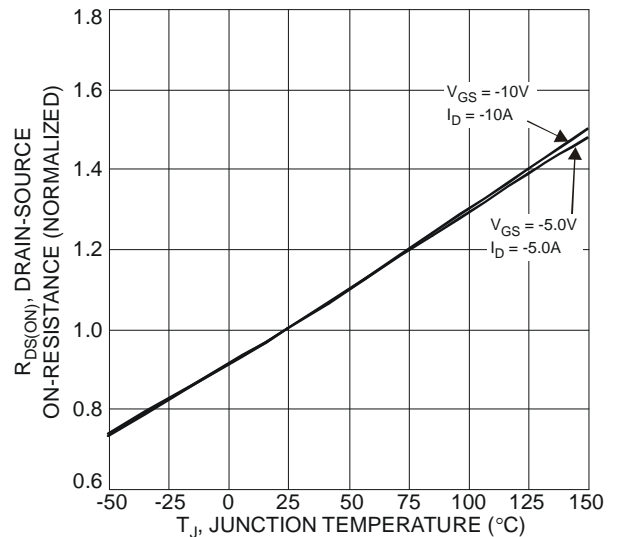


Figure 6 On-Resistance Variation with Temperature

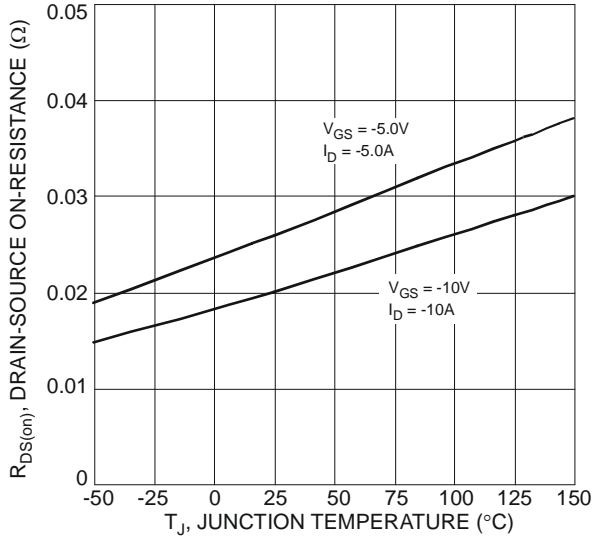


Figure 7 On-Resistance Variation with Temperature

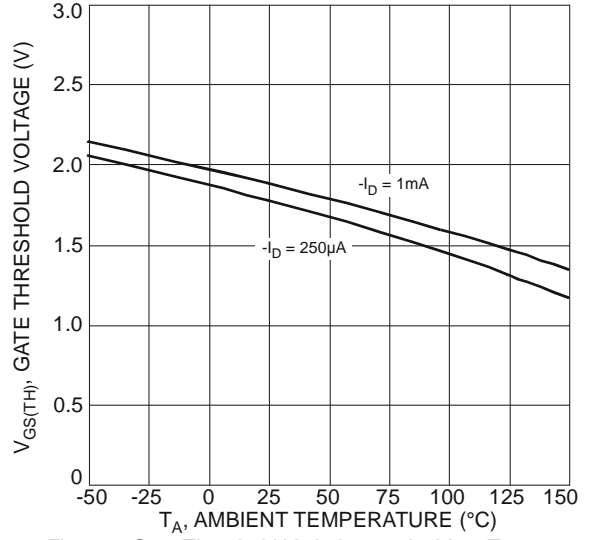


Figure 8 Gate Threshold Variation vs. Ambient Temperature

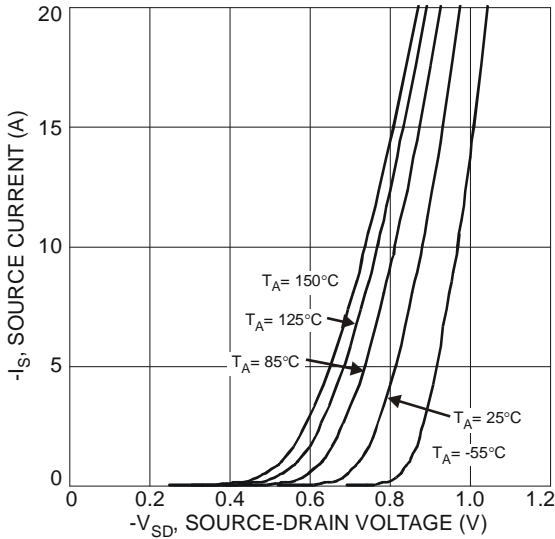


Figure 9 Diode Forward Voltage vs. Current

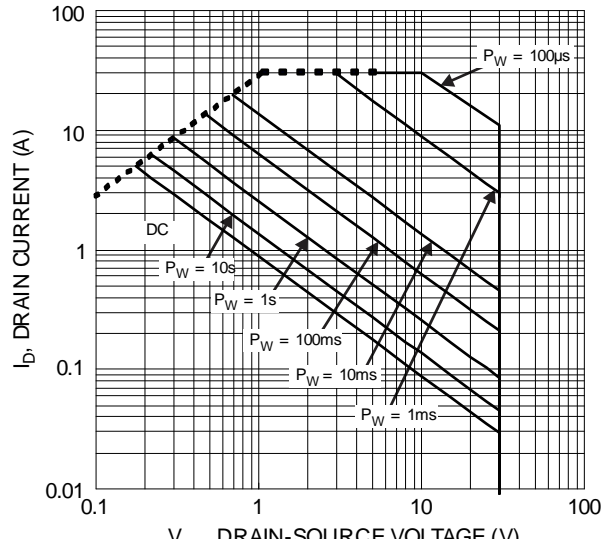


Figure 10 SOA, Safe Operation Area

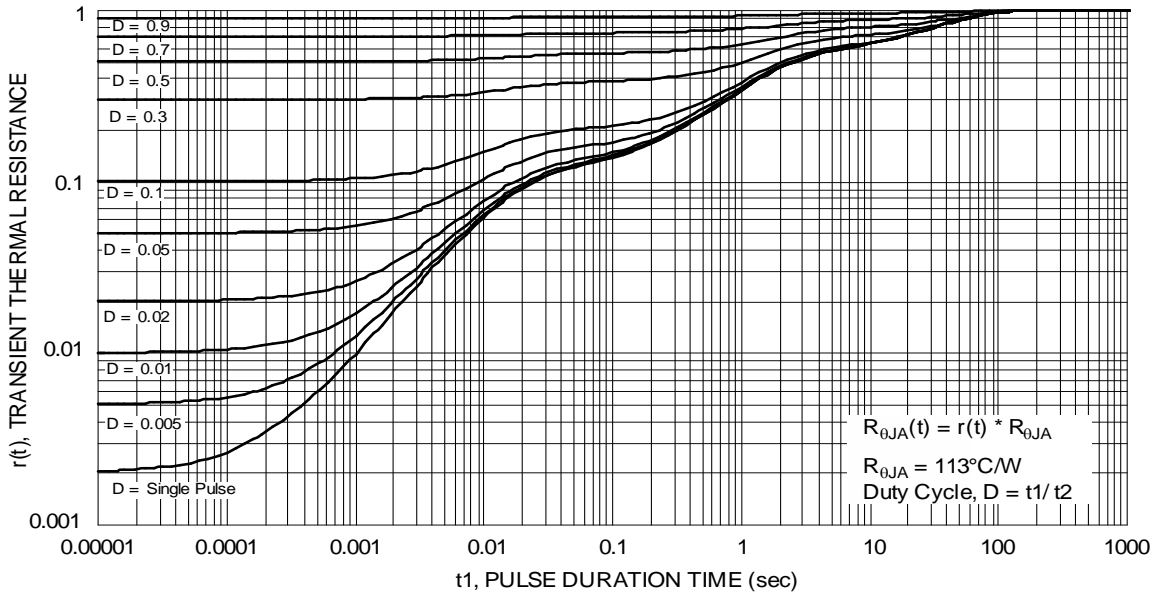
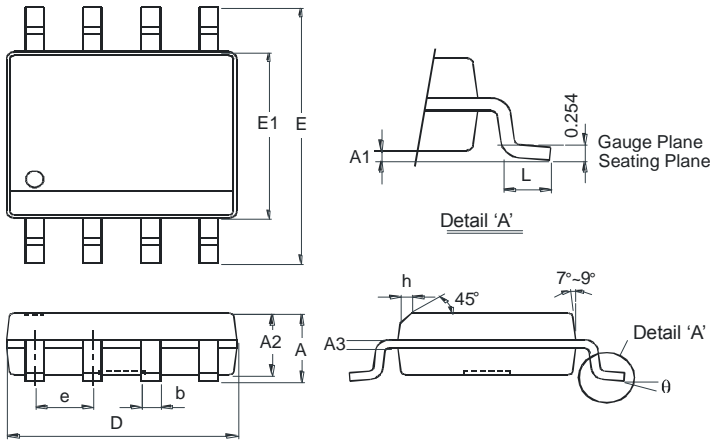


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

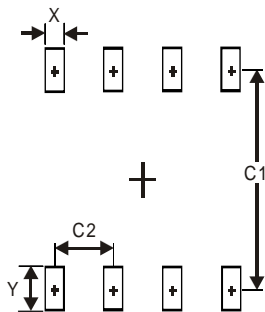
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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